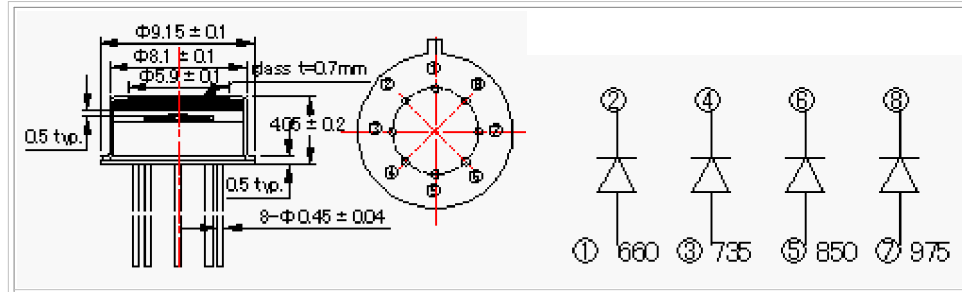


L660/735/850/975-40Q96-I Multi-wavelength LED

L660/735/850/975-40Q96-I consists of an AlGaAs' (660, 735, 850nm) and GaAs' (975nm)

LED mounted on TO-5 stem with a flat glass can/

†Outer dimension



†Specifications

1)Product No.	Multi-wavelength LED Lamp
2)type No.	L660/735/850//975-40Q96-I
3)Chip	
(1)Chip material	GaAlAs GaAs
(2)Peak wavelength	660,735,850,975nm
4)Package	
(1)stem type	TO-18 5pin type stem
(2)Lens	flat glass

†Absolute Maximum Ratings Ta=25 °C

Item	Symbol	Maximum Rated Value				Unit
		660	735	850	975	
Power Dissipation	PD	120	200	170	140	mW
Forward Current	IF	50	100	100	100	mA
Pulse Forward Current	IFP	200	500	500	500	mA
Reverse Voltage	VR	5				V
Operating Temperature	TOPR	-20~+80				°C
Storage Temperature	TSTG	-30~+100				°C
Soldering Temperature	TSOL	240				°C

†Electro-Optical Characteristics(Ta=25 °C)

Item		Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	660nm	VF	IF=20mA		1.90	2.30	V
	735nm				1.70	2.00	
	850nm				1.40	1.70	
	975nm				1.25	1.40	
Reverse Current		IR	VR=5V			10	uA
Total Radiation Power	660nm	Po	IF=20mA	0.8	1.5		mW
	735nm			1.5	3.0		
	850nm			2.0	3.4		
	975nm			0.3	0.7		
Peak Wavelength	660nm	ēP	IF=20mA		660		nm
	735nm				735		
	850nm				850		
	975nm				975		
	660nm				20		

Half Width	735nm	ë	IF=20mA		30		nm
	850nm				40		
	975nm				50		

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